

PUMD13-Q

NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

25 October 2021

Product data sheet

1. General description

NPN/PNP double Resistor-Equipped Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- · Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs
- Qualified according to AEC-Q101 and recommended for use in automotive applications

3. Applications

- Low current peripheral driver
- · Control of IC inputs
- · Replaces general-purpose transistors in digital applications

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor;	Per transistor; for the PNP transistor (TR2) with negative polarity where applicable							
V _{CEO}	collector-emitter voltage	open base		-	-	50	V	
I _O	output current			-	-	100	mA	
R1	bias resistor 1		[1]	3.3	4.7	6.1	kΩ	
R2/R1	bias resistor ratio		[1]	8	10	12		

[1] See section "Test information" for resistor calculation and test conditions.



NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2	0	TR1 R2 R1
6	O1	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	
				GND1 I1 O2 006aaa143

6. Ordering information

Table 3. Ordering information

Type number			
	Name	Description	Version
PUMD13-Q		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD13-Q	3%1

[1] % = placeholder for manufacturing site code

NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

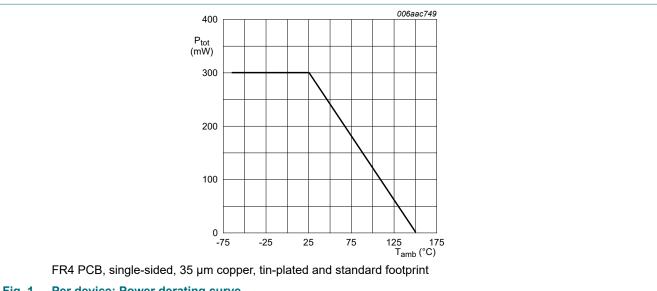
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or; for the PNP transistor (TF	(2) with negative polarity where appli	cable	<u> </u>		
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
V _I	input voltage	positive (input voltage TR1)		-	30	V
		negative (input voltage TR1)		-	-5	V
		positive (input voltage TR2)		-	5	V
		negative (input voltage TR2)		-	-30	V
lo	output current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	200	mW
Per device	<u> </u>		'	<u> </u>		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	er transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

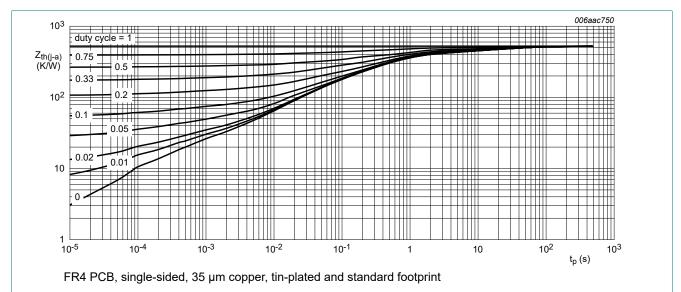


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

10. Characteristics

Table 7. Characteristics

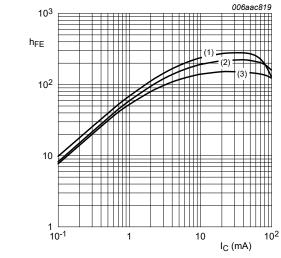
 T_{amb} = 25 °C, unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transist	tor; for the PNP transistor ((TR2) with negative polarity where appl	icable				
V _{(BR)CBO}	collector-base breakdown voltage	I _C = 100 μA; I _E = 0 A		50	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	I _C = 2 mA; I _B = 0 A		50	-	-	V
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}$		-	-	100	nA
I _{CEO}	collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A		-	-	1	μA
	current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A		-	-	170	μΑ
h _{FE}	DC current gain	V _{CE} = 5 V; I _C = 10 mA		100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}$		-	-	100	mV
$V_{I(off)}$	off-state input voltage	V _{CE} = 5 V; I _C = 100 μA		-	0.6	0.5	V
V _{I(on)}	on-state input voltage	V _{CE} = 0.3 V; I _C = 5 mA		1.3	0.9	-	V
R1	bias resistor 1		[1]	3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		[1]	8	10	12	
TR1 (NPN)				·			
C _c	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz		-	-	2.5	pF
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz	[2]	-	230	-	MHz
TR2 (PNP)				-			,
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz		-	-	3	pF
f _T	transition frequency	V _{CE} = -5 V; I _C = -10 mA; f = 100 MHz	[2]	-	180	-	MHz

^[1] See section "Test information" for resistor calculation and test conditions.

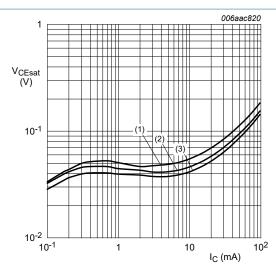
^[2] Characteristics of built-in transistor

NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω



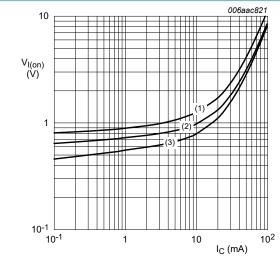
V_{CE} = 5 V (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $I_{C}/I_{B} = 20$ (1) $T_{amb} = 100 \, ^{\circ}C$ (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 4. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



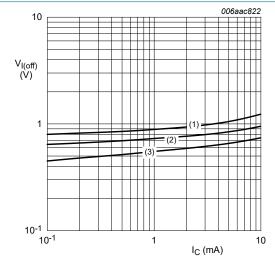
 V_{CE} = 0.3 V

(1) T_{amb} = -40 °C

(2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 5. TR1 (NPN): On-state input voltage as a function | Fig. 6. of collector current; typical values



 $V_{CE} = 5 V$

(1) $T_{amb} = -40 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): Off-state input voltage as a function of collector current; typical values

NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

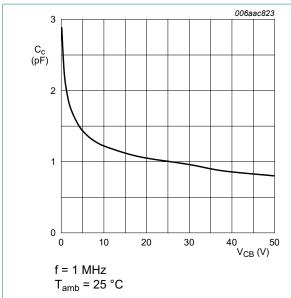
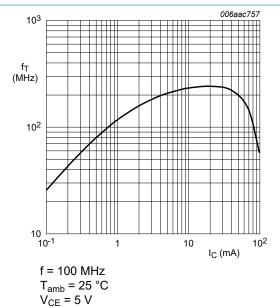
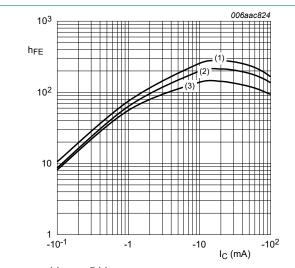


Fig. 7. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



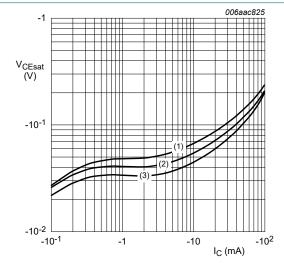
V_{CE} = 5 V

Fig. 8. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



 $V_{CE} = -5 V$ (1) $T_{amb} = 100 \,^{\circ}C$ (2) $T_{amb} = 25 \,^{\circ}C$ (3) $T_{amb} = -40 \,^{\circ}C$

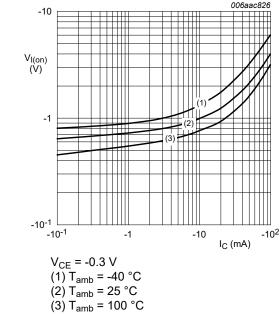
Fig. 9. TR2 (PNP): DC current gain as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1) $T_{\rm amb} = 100~{\rm ^{\circ}C}$ (2) $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3) $T_{\rm amb} = -40~{\rm ^{\circ}C}$

Fig. 10. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values

NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω



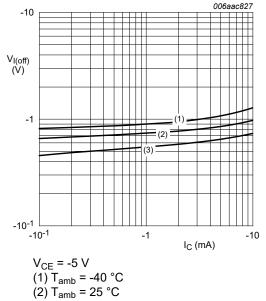
$$V_{CE} = -0.3 \text{ V}$$

$$(1) T_{amb} = -40 °C$$

(2)
$$I_{amb} = 25 \,^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

of collector current; typical values

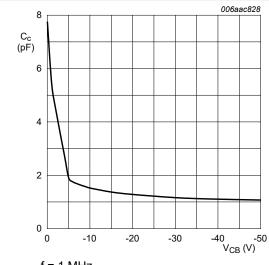


$$(1) I_{amb} = -40 °($$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

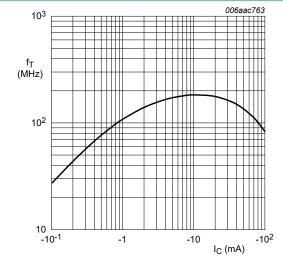
(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig. 11. TR2 (PNP): On-state input voltage as a function | Fig. 12. TR2 (PNP): Off-state input voltage as a function of collector current; typical values



f = 1 MHz T_{amb} = 25 °C

Fig. 13. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz

 T_{amb} = 25 °C $V_{CE} = -5 V$

Fig. 14. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

11. Test information

Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

Resistor calculation

• Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

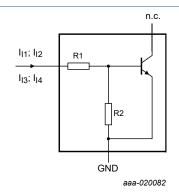


Fig. 15. NPN transistor: Resistor test circuit

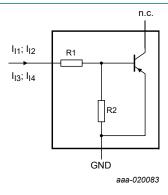


Fig. 16. PNP transistor: Resistor test circuit

Resistor test conditions

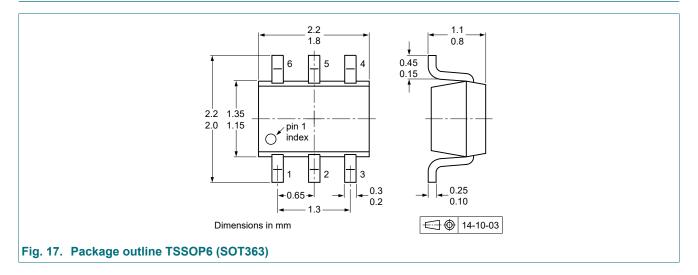
Table 8. Resistor test conditions

Type number	est conditions					
	I ₁₁	I _{I2}	I _{I3}	I ₁₄		
PUMD13-Q	90 μΑ	140 μΑ	-55 μA	-105 μA		
PUMD13-Q	-90 μA	-140 μA	55 μA	105 μΑ		

PUMD13-Q

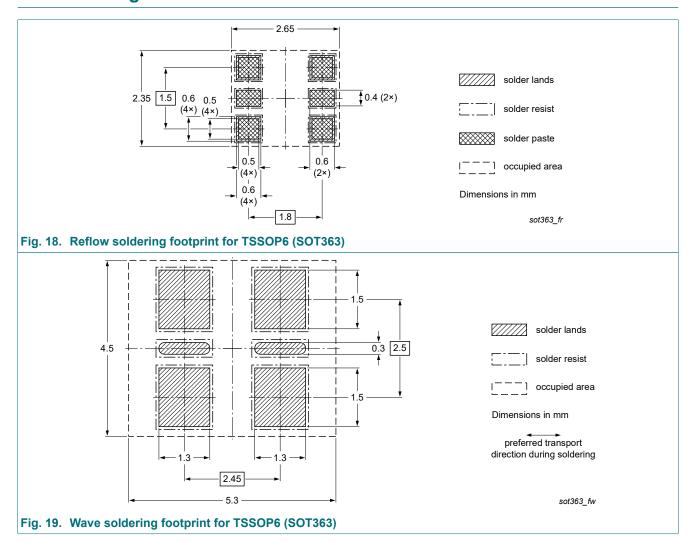
NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

12. Package outline



NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

13. Soldering



NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

14. Revision history

Table 9. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PUMD13-Q v.1	20211025	Product data sheet	-	-

NPN/PNP resistor-equipped double transistor; R1 = 4.7 k Ω , R2 = 47 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PUMD13-Q

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